## NSN 5961-01-375-1418

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View Online at https://aerobasegroup.com/nsn/5961-01-375-1418 **Inclosure Material:** Metal **Overall Length:** Between 0.330 inches and 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Electrostatic sensitive and hermetically sealed case **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.0 forward voltage, peak and 3.0 gate trigger voltage, dc **Current Rating Per Characteristic:** 16.00 amperes average on-state current, 180 degrees conduction angle, average over a full 60-hz cycle **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Hci & esd; junction pattern arrangement: pnpn **Nuclear Hardness Critical Feature:** Hardened **Special Test Features:** Selected and tested for application in radiation hardness critical systems **Thread Series Designator:** Unf **Terminal Type And Quantity:** 28 tab, solder lug and 1 threaded stud **Specification Data:** 81349-mil-s-19500/108 government specification Shelf Life: N/a

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**Unit Of Measure:** 

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Demilitarization:

No

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